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IN THE CLAIMS

Claims 1-10 (Canceled).

11 (Previously Presented). A method comprising:
using 1,2,4,5-tetraaza-3,6-disilacyclohexane as a silicon precursor to form silicon
nitride film at a temperature less than 500°C.

Claims 12-18 (Canceled).

19 (Original). The method of claim 11 further including using a nitrogen precursor
selected from one of ammonia, a hydrazine or a substituted hydrazine.

20 (Original). The method of claim 19 further including combining said silicon precursor
and said nitrogen precursor in a premixed cocktail with an optional solvent.

Claims 21-36 (Canceled).